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ABSTRACT OF THE DISCLOSURE

In a light emitting diode, a light-emitting region is including an active layer provided between a first conductivity type cladding layer formed on the semiconductor substrate and a second conductivity type cladding layer. A transparent conductive film made of a metal oxide is located over the light-emitting region. A layer for preventing exfoliation of the transparent conductive film, the preventing layer being made of a compound semiconductor contains at least aluminum and is located between the light-emitting region and the transparent conductive film. The layer for preventing exfoliation of the transparent conductive film contains a conductivity type determining ~~determination~~ impurity in a concentration of $1 \times 10^{19} \text{ cm}^{-3}$ or higher.

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